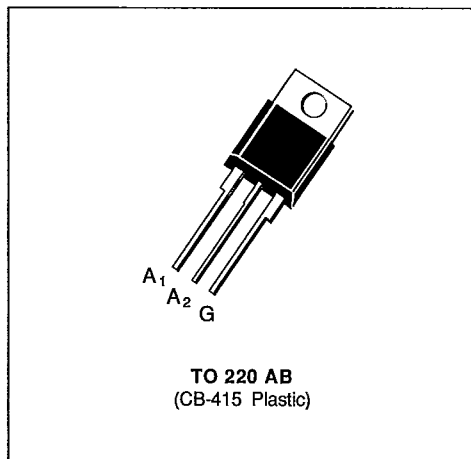


SNUBBERLESS TRIACS

- $I_{RMS} = 8\text{ A}$ at $T_c = 90\text{ }^{\circ}\text{C}$.
- $V_{DRM} : 200\text{ V}$ to 800 V .
- $I_{GT} = 75\text{ mA}$ (QI-II-III).
- GLASS PASSIVATED CHIP.
- HIGH SURGE CURRENT : $I_{TSM} = 80\text{ A}$.
- HIGH COMMUTATION CAPABILITY :
 $(di/dt)_c > 10\text{ A/ms}$ without snubber.
- INSULATING VOLTAGE : 2500 V_{RMS} .

**DESCRIPTION**

New range suited for applications such as phase control and static switching on inductive or resistive load.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
I_{RMS}	RMS on-state current (360 ° conduction angle)	$T_c = 90\text{ }^{\circ}\text{C}$	8	A
I_{TSM}	Non repetitive surge peak on-state current (T_J initial = $25\text{ }^{\circ}\text{C}$)	$t = 8.3\text{ ms}$	85	A
		$t = 10\text{ ms}$	80	
I^2t	I^2t value	$t = 10\text{ ms}$	32	A^2s
di/dt	Critical rate of rise of on-state current (1)	Repetitive $F = 50\text{ Hz}$	20	$\text{A}/\mu\text{s}$
		Non Repetitive	100	
T_{stg} T_J	Storage and operating junction temperature range		- 40, + 150 - 40, + 125	$^{\circ}\text{C}$ $^{\circ}\text{C}$

Symbol	Parameter	BTA 08-					Unit
		200 AW	400 AW	600 AW	700 AW	800 AW	
V_{DRM}	Repetitive peak off-state voltage (2)	± 200	± 400	± 600	± 700	± 800	V

(1) Gate supply : $I_G = 750\text{ mA}$ – $di_G/dt = 1\text{ A}/\mu\text{s}$.

(2) $T_J = 125\text{ }^{\circ}\text{C}$.

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THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient	60	°C/W
$R_{th(j-c)}$ DC	Junction to case for DC	4.3	°C/W
$R_{th(j-c)}$ AC	Junction to case for 360 ° conduction angle ($F = 50$ Hz)	3.2	°C/W

GATE CHARACTERISTICS (maximum values)

 $P_{GM} = 40$ W ($t = 10$ μ s) $P_{G(AV)} = 1$ W $I_{GM} = 4$ A ($t = 10$ μ s) $V_{GM} = 16$ V ($t = 10$ μ s).

SGS-THOMSON

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Quadrants	Min.	Typ.	Max.	Unit
I _{GT}	T _J = 25 °C Pulse duration > 20 μs	V _D = 12 V	R _L = 33 Ω	I-II-III	2		75	mA
V _{GT}	T _J = 25 °C Pulse duration > 20 μs	V _D = 12 V	R _L = 33 Ω	I-II-III			1.5	V
V _{GD}	T _J = 125 °C Pulse duration > 20 μs	V _D = V _{DRM}	R _L = 3.3 kΩ	I-II-III	0.2			V
I _H *	T _J = 25 °C Gate open	I _T = 100 mA R _L = 140 Ω					75	mA
I _L	T _J = 25 °C Pulse duration > 20 μs	V _D = 12 V	I _G = 500 mA	I-III		75		mA
				II		150		
V _{TM} *	T _J = 25 °C	I _{TM} = 11 A	t _p = 10 ms				1.75	V
I _{DRM} *	T _J = 25 °C	V _{DRM} rated	Gate open				0.01	mA
	T _J = 125 °C						2	
dv/dt *	T _J = 125 °C Linear slope up to 0.67 V _{DRM}	Gate open			750	1000		V/μs
(di/dt) _c *	T _J = 125 °C Without snubber	V _{DRM} rated			10	20		A/ms
t _{gt}	T _J = 25 °C I _T = 11 A	di _G /dt = 3.5 A/μs V _D = V _{DRM}	I _G = 500 mA	I-II-III		2		μs

* For either polarity of electrode A_2 voltage with reference to electrode A_1 .

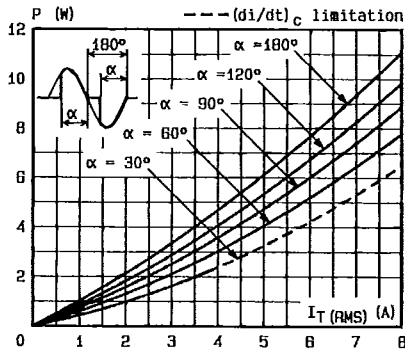


Fig.1 - Maximum mean power dissipation versus RMS on-state current ($F = 60$ Hz).

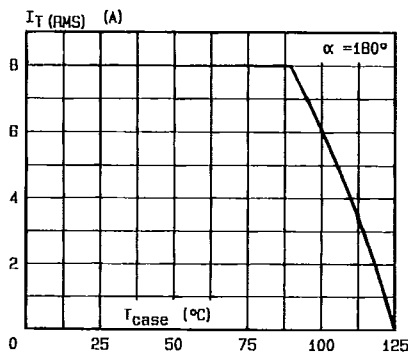


Fig.3 - RMS on-state current versus case temperature.

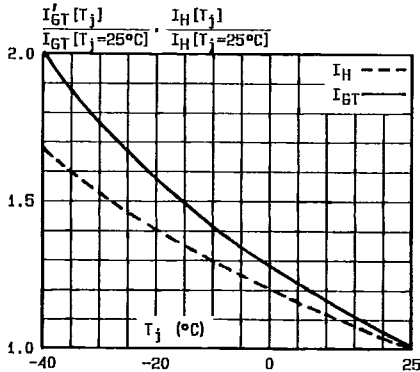


Fig.5 - Relative variation of gate trigger current and holding current versus junction temperature.

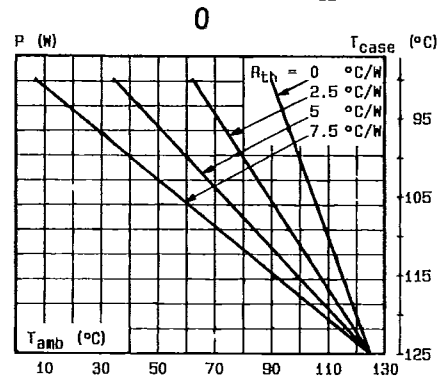


Fig.2 - Correlation between maximum mean power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

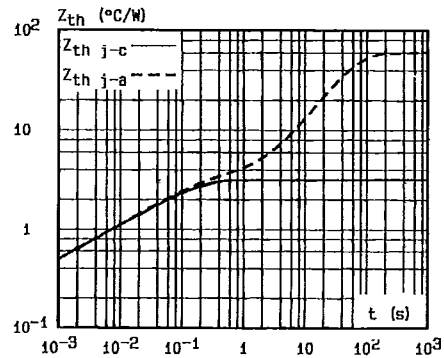


Fig.4 - Thermal transient impedance junction to case and junction to ambient versus pulse duration.

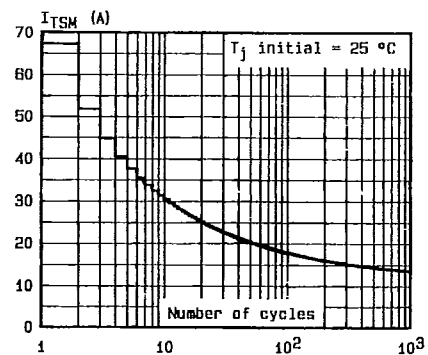


Fig.6 - Non repetitive surge peak on-state current versus number of cycles.

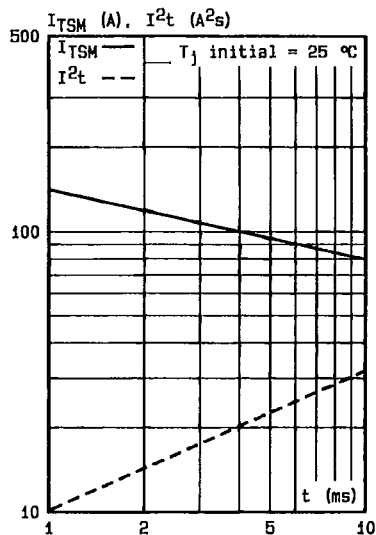


Fig.7 - Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10$ ms, and corresponding value of I^2t .

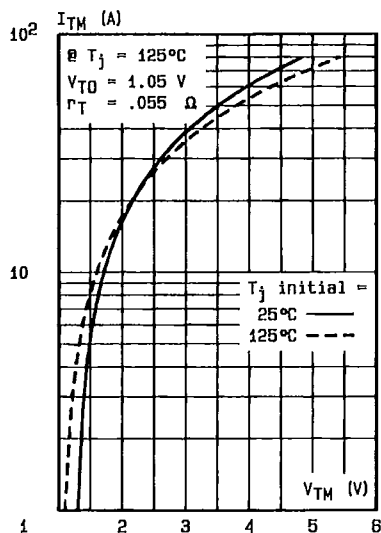
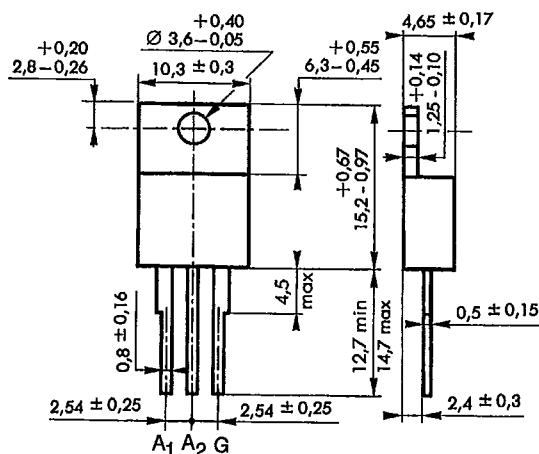


Fig.8 - On-state characteristics (maximum values).

PACKAGE MECHANICAL DATA

TO 220 AB (CB-415) Plastic



Cooling method : by conduction (method C)

Marking : type number

Weight : 2 g